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HMC505* Product Page Quick Links

Last Content Update: 11/01/2016

Comparable Parts

View a parametric search of comparable parts

Evaluation Kits <a> □

• HMC505LP4 Evaluation Board

Documentation <a>□

Data Sheet

• HMC505 Data Sheet

Reference Materials 🖵

Quality Documentation

- Package/Assembly Qualification Test Report: LP4, LP4B, LP4C, LP4K (QTR: 2013-00487 REV: 04)
- Package/Assembly Qualification Test Report: Plastic Encapsulated QFN (QTR: 05006 REV: 02)
- Semiconductor Qualification Test Report: GaAs HBT-A (QTR: 2013-00228)

Design Resources -

- HMC505 Material Declaration
- · PCN-PDN Information
- · Quality And Reliability
- · Symbols and Footprints

Discussions <a>□

View all HMC505 EngineerZone Discussions

Sample and Buy 🖳

Visit the product page to see pricing options

Technical Support <a> □

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HMC505LP4 / 505LP4E

MMIC VCO w/ BUFFER AMPLIFIER, 6.8 - 7.4 GHz



Typical Applications

Low noise MMIC VCO w/Buffer Amplifier for:

- VSAT & Microwave Radio
- Test Equipment & Industrial Controls
- Military

Features

Pout: +11dBm

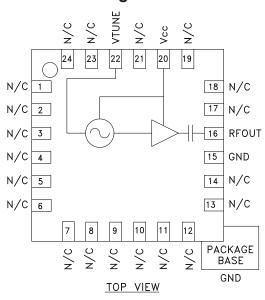
Phase Noise: -106 dBc/Hz @100 kHz

No External Resonator Needed

Single Supply: +3V @ 80 mA

QFN Leadless SMT Package, 16mm²

Functional Diagram



General Description

The HMC505LP4 & HMC505LP4E are GaAs InGaP Heterojunction Bipolar Transistor (HBT) MMIC VCOs with integrated resonators, negative resistance devices, varactor diodes, and buffer amplifiers. Covering 6.8 to 7.4 GHz, the VCO's phase noise performance is excellent over temperature, shock and vibration due to the oscillator's monolithic structure. Power output is +11 dBm typical from a single supply of +3V @ 80 mA. The voltage controlled oscillator is packaged in a leadless QFN 4x4 mm surface mount package.

Electrical Specifications, $T_{\Delta} = +25^{\circ}$ C, Vcc = +3V

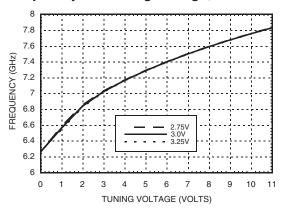
Parameter	Min.	Тур.	Max.	Units
Frequency Range	6.8 - 7.4			GHz
Power Output	8	11		dBm
SSB Phase Noise @ 100 kHz Offset, Vtune= +5V @ RF Output		-106		dBc/Hz
Tune Voltage (Vtune)	1		11	V
Supply Current (Icc) (Vcc = +3.0V)		80		mA
Tune Port Leakage Current			10	μA
Output Return Loss		9		dB
Harmonics 2nd 3rd		-19 -28		dBc dBc
Pulling (into a 2.0:1 VSWR)		6		MHz pp
Pushing @ Vtune= +5V		20		MHz/V
Frequency Drift Rate		0.8		MHz/°C



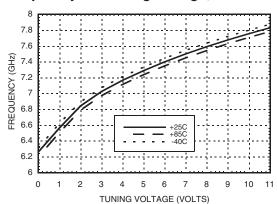


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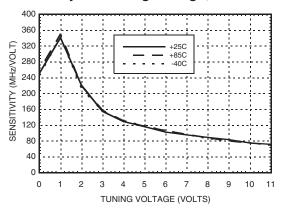
Frequency vs. Tuning Voltage, T= 25°C



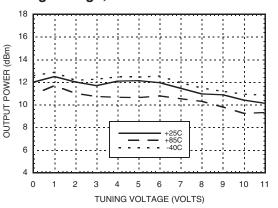
Frequency vs. Tuning Voltage, Vcc= +3V



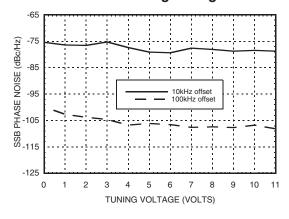
Sensitivity vs. Tuning Voltage, Vcc= +3V



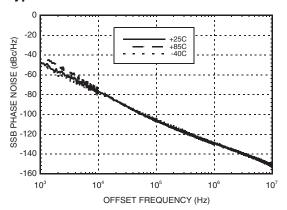
Output Power vs.
Tuning Voltage, Vcc= +3V



Phase Noise vs. Tuning Voltage



Typical SSB Phase Noise @ Vtune= +5V





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Typical Supply Current vs. Vcc

Vcc (V)	Icc (mA)
2.75	70
3.0	80
3.25	90

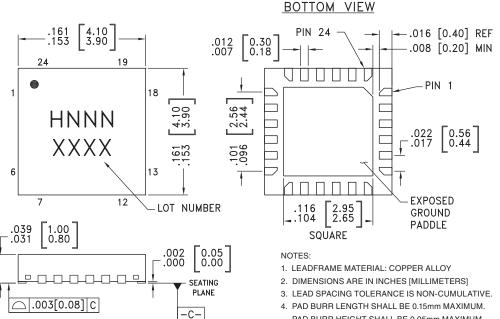
Note: VCO will operate over full voltage range shown above.



Absolute Maximum Ratings

Vcc	+3.5 Vdc	
Vtune	0 to +11V	
Channel Temperature	135 °C	
Continuous Pdiss (T = 85°C) (derate 6.31 mW/°C above 85°C)	315 mW	
Thermal Resistance (R _{TH}) (junction to package base)	158 °C/W	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-40 to +85 °C	
ESD Sensitivity (HBM)	Class 1A	

Outline Drawing



- PAD BURR HEIGHT SHALL BE 0.05mm MAXIMUM.
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05mm.
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
- 7. REFER TO HITTITE APPLICATION NOT FOR SUGGESTED LAND PATTERN.

Package Information

Part Number	Package Body Material Lead Finish MSL Rat		MSL Rating	Package Marking [3]
HMC505LP4	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 [1]	H505 XXXX
HMC505LP4E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	H505 XXXX

- [1] Max peak reflow temperature of 235 °C
- [2] Max peak reflow temperature of 260 $^{\circ}\text{C}$
- [3] 4-Digit lot number XXXX





MMIC VCO w/ BUFFER AMPLIFIER, 6.8 - 7.4 GHz

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1- 14, 17 - 19, 21, 23, 24	N/C	No Connection. These pins may be connected to RF ground. Performance will not be affected.	
15	GND	This pin must be connected to RF & DC ground.	♥ GND =
16	RFOUT	RF output (AC coupled)	—
20	Vcc	Supply Voltage Vcc= 3V	Vcc O
22	VTUNE	Control Voltage Input. Modulation port bandwidth dependent on drive source impedance.	VTUNE 0 150 0 C;= 7.8pF
	GND	Package bottom has an exposed metal paddle that must be RF & DC grounded.	○ GND =

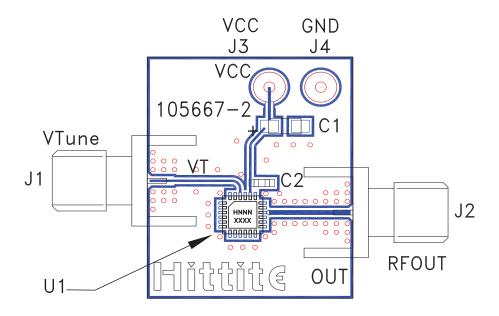


HMC505LP4 / 505LP4E

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EARTH FRIENDLY

Evaluation PCB



List of Materials for Evaluation PCB 105706 [1]

Item	Description
J1 - J2	PCB Mount SMA RF Connector
J3 - J4	DC Pin
C1	4.7 μF Tantalum Capacitor
C2	10,000 pF Capacitor, 0603 Pkg.
U1	HMC505LP4 / HMC505LP4E VCO
PCB [2]	105667 Eval Board

[1] Reference this number when ordering complete evaluation PCB $\,$

[2] Circuit Board Material: Rogers 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.



ROHS V

Notes:

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